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- Deposition
  - Depositing a material onto a substrate
    - Thick oxide layers (where growth by oxidation is not reasonable)
    - Polysilicon (Gate material)
    - Special materials (Si<sub>3</sub>N<sub>4</sub>, SiC)
  - Chemical Vapor Deposition
    - Chemical processes are used to deposit material
  - Physical Vapor Deposition
    - Mechanical processes are used to deposit material

- Chemical Vapor Deposition
  - Gases are decomposed into constituent elements
  - The desired constituents then "settle" onto the surface of the wafer
    - Conformity how the desired material covers vertical vs horizontal surfaces
      - K = RateV / RateH



- Chemical Vapor Deposition
  - Atmospheric Pressure CVD (APCVD)
    - Results in low density material
    - Used for Oxide deposition
      SiH<sub>4</sub> + O<sub>2</sub> <-> SiO<sub>2</sub> + 2H<sub>2</sub>



- Chemical Vapor Deposition
  - Low Pressure CVD (LPCVD)
    - Results in high density material
    - Conformality is high due to the low pressure allows for more random particle movement
    - Used for thin films

 $4 \text{ NH}_3 + 3 \text{ SiH}_2\text{Cl}_2 \iff \text{Si}_3\text{N}_4 + 6 \text{ HCl} + 6 \text{ H}_2$ 

- Chemical Vapor Deposition
  - Plasma Enhanced CVD (PECVD)
    - Low temperature version of CVD
    - Gasses are decomposed (a plasma)by using a high frequency voltage
    - Used to put films on top of metal layers
      - metal cannot take the heat from other methods



src: samcointl.com

- Physical Vapor Deposition
  - Sputtering
    - A sample of the desired material is bombarded with ions
    - The released particles then "settle" on to the wafer surface



Src: www.halbleiter.org